



# SPECIFICATION

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**DM3S4G18AB2-SEMAY**  
**4GB DDR3 1866MHz SODIMM I-Temp**  
**K4B4G1646E-BMMA**  
DDR3- 1866, 4Gb (512\*8), PCB: KO8096

Version: 1.0

Date: 09.11.2020

Note: This specification is subject to change without prior notice

## Nomenclature for Data Modul DIMMs

max length of P/N 18 digits

DM	4	S	4G	266	B	6	-	ND	HR	I
<b>DM</b>	DM- : Data Modul									
<b>Technology</b>	0 : SDR SDRAM 1 : DDR SDRAM 2 : DDR2 SDRAM 3 : DDR3 SDRAM 4 : DDR4 SDRAM 5 : DDR5 SDRAM									
<b>Module Type</b>	A : ECC DIMM (x72) D : DIMM non ECC unbuffered E : ECC SO-DIMM (x72) F : fully buffered DIMM L : LR DIMM (load reduced) Q : ECC RDIMM R : registered DIMM S : SO-DIMM unbuffered U : VLP DIMM non ECC unbuffered V : VLP RDIMM W : VLP ECC DIMM O : others									
<b>Density</b>	128 : 128 MB 256 : 256 MB 512 : 512 MB 1G : 1 GB 2G : 2 GB 4G : 4 GB 8G : 8 GB 16G : 16 GB 32G : 32 GB									
<b>Speed / Performance</b>	013 : SDR PC 133 020 : SDR PC 200 333 : DDR1 300 400 : DDR1 400 x: PCB option    667 / 66x : DDR2 667 800 / 80x : DDR2 800 106 / 10x : DDR3 1066 133 / 13x : DDR3 1333 160 / 16x : DDR3 1600 186 / 18x : DDR3 1866 213 / 21x : DDR4 2133 240 / 24x : DDR4 2400 266 / 26x : DDR4 2666 293 / 29x : DDR4 2933 320 / 32x : DDR4 3200									
<b>Component Organisation</b>	A : x4 B : x8 C : x16 D : other organisations									
<b>Number of Components</b>	1 : 4 Chips 2 : 8 Chips 3 : 16 Chips 4 : 32 Chips 6 : 9 Chips 7 : 18 Chips 8 : 36 Chips									
<b>Separator btw Product and Componet Manufacturer Data</b>										
<b>Component Mfr. Die Rev.</b>	M : Micron H : SK Hynix N : Nanya S : Samsung E : Etron W : Winbond									
<b>Speed / Performance of Component (as metioned on the DRAM)</b>										
<b>Special Fuctions</b>	Blank : not specified I : industrial temperature Y : low power & extended temperature L : low power									

## Description

Data Modul Unbuffered Small Outline DDR3L SDRAM DIMMs (Unbuffered Small Outline Double Data Rate Synchronous DRAM Dual In-Line Memory Modules) are low power, high-speed operation memory modules that use DDR3L SDRAM devices. These Unbuffered DDR3L SDRAM SODIMMs are intended for use as main memory when installed in systems such as mobile personal computers.

## Features

- Power Supply: VDD=±1.35V (1.283V to 1.45V)
- VDDQ=+1.35V (1.283V to 1.45V)
- VDDSPD=3.0V to 3.6V
- Backward compatible with 1.5V DDR3 Memory Module
- 8 internal banks
- Data transfer rates: PC3-10600, PC3-12800, PC3-14900
- Programmable CAS Latency: 6, 7, 8, 9, 10, 11, 13
- Programmable /CAS Write Latency (CWL) =5, 6, 7, 8, 9
- Bi-directional Differential Data Strobe
- 8 bit pre-fetch
- Burst Length (BL) switch on-the-fly: BL 8 or BC (Burst Chop) 4
- On Die Termination (ODT) supported
- This product is in Compliance with the RoHS directive
- Internal calibration through ZQ pin
- Asynchronous reset

Symbol	Parameter	Rating	Units
T <sub>OPR</sub>	Operating temperature (ambient)	-40 to 95	°C
H <sub>OPR</sub>	Operating humidity (relative)	10 to 90	%

		Rating	
T <sub>OPER</sub>	Normal Operating Temperature Range	-40 to 95	°C
	Extended Temperature Range	85 to 95	

## Pin Configurations

Pin #	Front Side	Pin #	Back Side	Pin #	Front Side	Pin #	Back Side	Pin #	Front Side	Pin #	Back Side	Pin #	Front Side	Pin #	Back Side
1	V <sub>REF</sub> DQ	2	V <sub>SS</sub>	53	DQ19	54	V <sub>SS</sub>	105	V <sub>DD</sub>	106	V <sub>DD</sub>	157	DQ42	158	DQ46
3	V <sub>SS</sub>	4	DQ4	55	V <sub>SS</sub>	56	DQ28	107	A10/AP	108	BA1	159	DQ43	160	DQ47
5	DQ0	6	DQ5	57	DQ24	58	DQ29	109	BA0	110	RAS <sup>—</sup>	161	V <sub>SS</sub>	162	V <sub>SS</sub>
7	DQ1	8	V <sub>SS</sub>	59	DQ25	60	V <sub>SS</sub>	111	V <sub>DD</sub>	112	V <sub>DD</sub>	163	DQ48	164	DQ52
9	V <sub>SS</sub>	10	DQS0	61	V <sub>SS</sub>	62	DQS3	113	WE <sup>—</sup>	114	SO <sup>—</sup>	165	DQ49	166	DQ53
11	DM0	12	DQS0	63	DM3	64	DQS3	115	CAS <sup>—</sup>	116	ODT0	167	V <sub>SS</sub>	168	V <sub>SS</sub>
13	V <sub>SS</sub>	14	V <sub>SS</sub>	65	V <sub>SS</sub>	66	V <sub>SS</sub>	117	V <sub>DD</sub>	118	V <sub>DD</sub>	169	DQS6	170	DM6
15	DQ2	16	DQ6	67	DQ26	68	DQ30	119	A13 <sup>2</sup>	120	ODT1	171	DQS6	172	V <sub>SS</sub>
17	DQ3	18	DQ7	69	DQ27	70	DQ31	121	S1 <sup>—</sup>	122	NC	173	V <sub>SS</sub>	174	DQ54
19	V <sub>SS</sub>	20	V <sub>SS</sub>	71	V <sub>SS</sub>	72	V <sub>SS</sub>	123	V <sub>DD</sub>	124	V <sub>DD</sub>	175	DQ50	176	DQ55
21	DQ8	22	DQ12	73	CKE0	74	CKE1	125	TEST	126	V <sub>REF</sub> CA	177	DQ51	178	V <sub>SS</sub>
23	DQ9	24	DQ13	75	V <sub>DD</sub>	76	V <sub>DD</sub>	127	V <sub>SS</sub>	128	V <sub>SS</sub>	179	V <sub>SS</sub>	180	DQ60
25	V <sub>SS</sub>	26	V <sub>SS</sub>	77	NC	78	A15 <sup>2</sup>	129	DQ32	130	DQ36	181	DQ56	182	DQ61
27	DQS1	28	DM1	79	BA2	80	A14 <sup>2</sup>	131	DQ33	132	DQ37	183	DQ57	184	V <sub>SS</sub>
29	DQS1	30	RESET	81	V <sub>DD</sub>	82	V <sub>DD</sub>	133	V <sub>SS</sub>	134	V <sub>SS</sub>	185	V <sub>SS</sub>	186	DQS7
31	V <sub>SS</sub>	32	V <sub>SS</sub>	83	A12/BC	84	A11	135	DQS4	136	DM4	187	DM7	188	DQS7
33	DQ10	34	DQ14	85	A9	86	A7	137	DQS4	138	V <sub>SS</sub>	189	V <sub>SS</sub>	190	V <sub>SS</sub>
35	DQ11	36	DQ15	87	V <sub>DD</sub>	88	V <sub>DD</sub>	139	V <sub>SS</sub>	140	DQ38	191	DQ58	192	DQ62
37	V <sub>SS</sub>	38	V <sub>SS</sub>	89	A8	90	A6	141	DQ34	142	DQ39	193	DQ59	194	DQ63
39	DQ16	40	DQ20	91	A5	92	A4	143	DQ35	144	V <sub>SS</sub>	195	V <sub>SS</sub>	196	V <sub>SS</sub>
41	DQ17	42	DQ21	93	V <sub>DD</sub>	94	V <sub>DD</sub>	145	V <sub>SS</sub>	146	DQ44	197	SA0	198	EVENT
43	V <sub>SS</sub>	44	V <sub>SS</sub>	95	A3	96	A2	147	DQ40	148	DQ45	199	V <sub>DD</sub> <sub>SPD</sub>	200	SDA
45	DQS2	46	DM2	97	A1	98	A0	149	DQ41	150	V <sub>SS</sub>	201	SA1	202	SCL
47	DQS2	48	V <sub>SS</sub>	99	V <sub>DD</sub>	100	V <sub>DD</sub>	151	V <sub>SS</sub>	152	DQS5	203	V <sub>TT</sub>	204	V <sub>TT</sub>
49	V <sub>SS</sub>	50	DQ22	101	CK0	102	CK1	153	DM5	154	DQS5				
51	DQ18	52	DQ23	103	CK0	104	CK1	155	V <sub>SS</sub>	156	V <sub>SS</sub>				

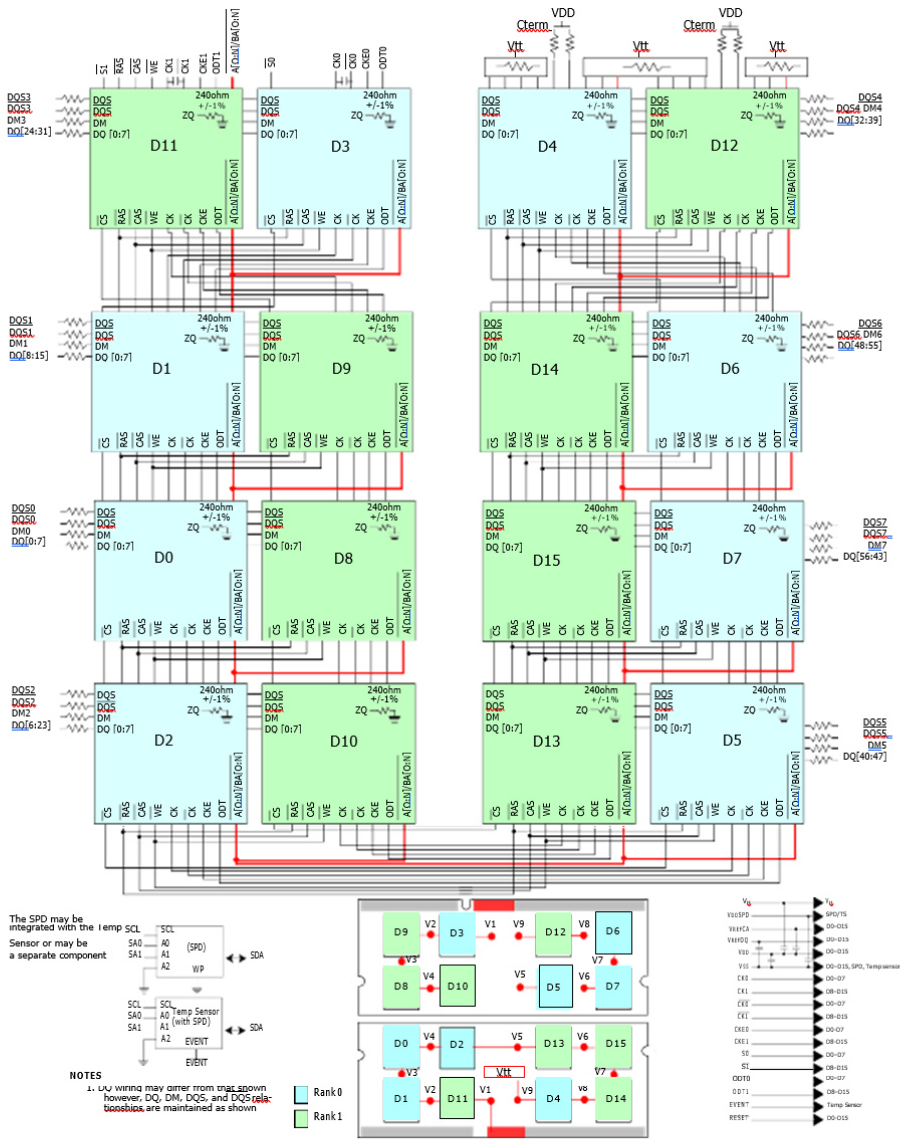
**NC = No Connect; RFU = Reserved Future Use**

1. TEST (pin 125) is reserved for bus analysis probes and is NC on normal memory modules.
2. This address might be connected to NC balls of the DRAMs (depending on density); either way they will be connected to the termination resistor.

## Pin Description

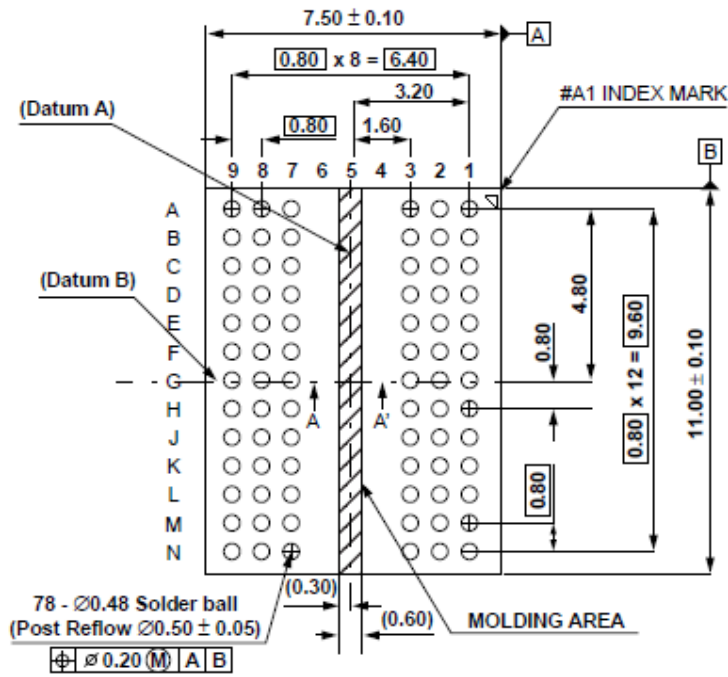
Pin Name	Description	Number	Pin Name	Description	Number
CK[1:0]	Clock Input, positive line	2	DQ[63:0]	Data Input/Output	64
$\overline{\text{CK}}[1:0]$	Clock Input, negative line	2	DM[7:0]	Data Masks	8
CKE[1:0]	Clock Enables	2	DQS[7:0]	Data strobes	8
$\overline{\text{RAS}}$	Row Address Strobe	1	$\overline{\text{DQS}}[7:0]$	Data strobes, negative line	8
$\overline{\text{CAS}}$	Column Address Strobe	1	$\overline{\text{EVENT}}$	Temperature event pin	1
$\overline{\text{WE}}$	Write Enable	1	TEST	Logic Analyzer specific test pin (No connect on SODIMM)	1
$\overline{\text{S}}[1:0]$	Chip Selects	2	$\overline{\text{RESET}}$	Reset Pin	1
A[9:0],A11, A[15:13]	Address Inputs	14	V <sub>DD</sub>	Core and I/O Power	18
A10/AP	Address Input/Autoprecharge	1	V <sub>SS</sub>	Ground	52
A12/ $\overline{\text{BC}}$	Address Input/Burst chop	1			
BA[2:0]	SDRAM Bank Addresses	3	V <sub>REFDQ</sub>	Input/Output Reference	1
ODT[1:0]	On Die Termination Inputs	2	V <sub>REFCA</sub>		1
SCL	Serial Presence Detect (SPD) Clock Input	1	V <sub>TT</sub>	Termination Voltage	2
SDA	SPD Data Input/Output	1	V <sub>DDSPD</sub>	SPD Power	1
SA[1:0]	SPD Address Inputs	2	NC	Reserved for future use	2
				<b>Total:</b>	<b>204</b>

## Functional Diagram

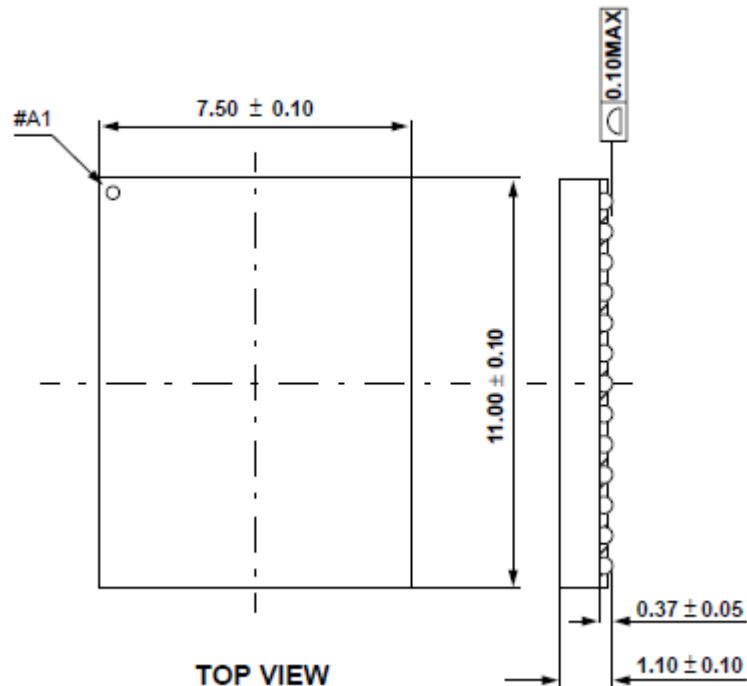


## Package Dimension

Units : Millimeters

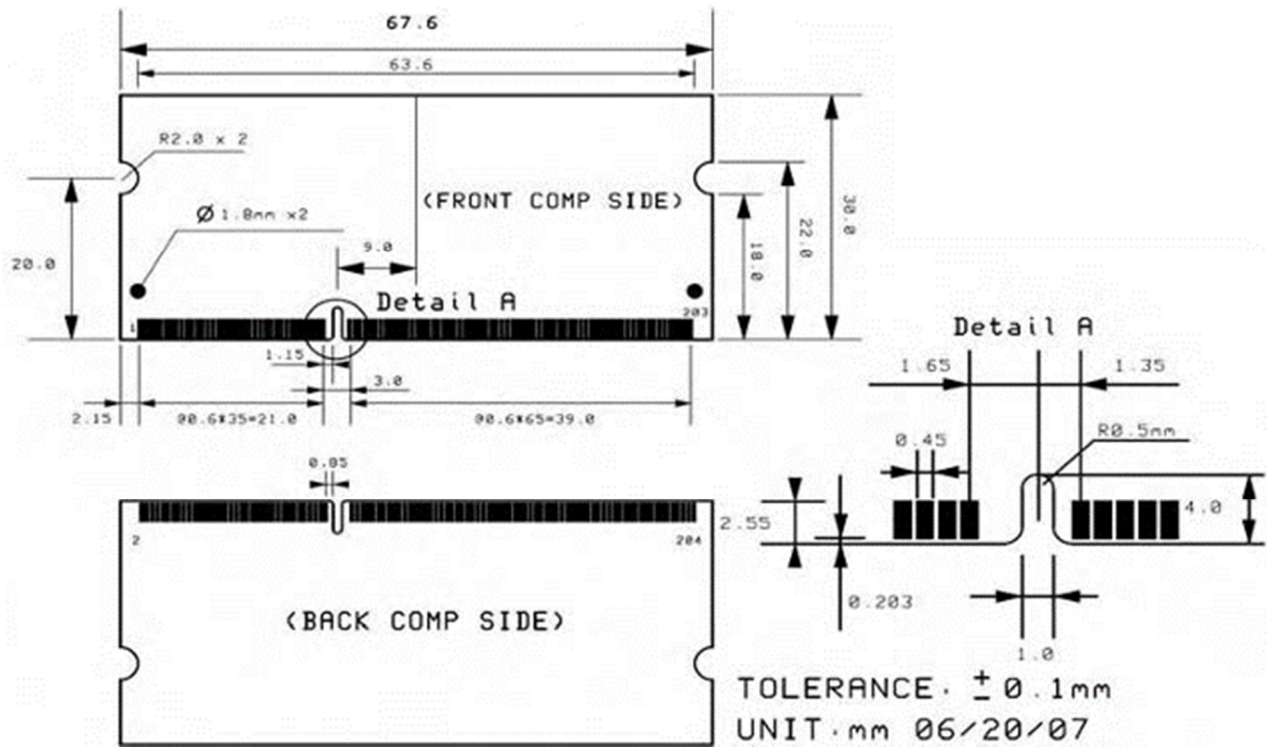


**BOTTOM VIEW**



**TOP VIEW**

## PCB Panelization







ALL TECHNOLOGIES. ALL COMPETENCIES. ONE SPECIALIST.



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